First-principles calculations to investigate optical properties of B _yAl _xIn _{1-x-y}N alloys for optoelectronic devices

Abstract

First-principles density-functional theory of Full-Potential Linear Augmented Plane Wave (FP-LAPW) within local density approximation (LDA) of the optical properties of B $_{\rm V}$ Al $_{\rm x}$ In $_{\rm 1- x-y}$ N systems (with x = 0.187 and y = 0.062, 0.125 and 0.187) has been performed. Substitutional atoms of Boron induced in small amounts into the (Al $_{\rm x}$ In $_{\rm 1-x}$)-cationic sublattice of AlInN affects the energy gap of BAIInN. The higher band gap of Al $_{\rm 0.375}$ In $_{\rm 0.625}$ N alloy can form a useful quantum well (QW) laser structure. A best choice of B-content, B $_{\rm V}$ Al $_{\rm x}$ In $_{\rm 1-x-y}$ N could be an alternative to Al $_{\rm x}$ In $_{\rm 1-x}$ N. The results of accurate calculations of the band structures and optical properties show the better performance characteristics belong to the structure containing B-content (y) of 12.5%. The NaCl metallic B $_{\rm y}$ Al $_{\rm 0.1875}$ In $_{\rm 0.8125-y}$ N has a direct character for y = 12.5%. The imaginary part of dielectric function, reflectivity, refractive index, absorption coefficient and optical conductivity are investigated well and provide reasonable results for optoelectronic devices applications.